## AMENDMENT

**In the Specification:**

Insert the following heading after the Title.

BACKGROUND OF THE INVENTION

Amend the heading at page 1, line 2 to read ~~Technical~~ Field of the Invention.

Amend the heading at page 1, line 6 to read ~~Conventional~~ Description of the Related Art.

Replace the heading at page 1, line 21, with the following new subtitle:

SUMMARY OF THE INVENTION

Delete the heading at page 2, line 2.

Amend the paragraph starting at page 3, line 27, to read as follows:

Fig. 21A shows ~~the simulation~~ measurement results of this invention, and Fig. 21B is a schematic plan view of an embodiment of this invention.

Amend the paragraph starting at page 3, line 31, to read as follows:

Fig. 23A is a schematic plan view of an embodiment of this invention, and Fig. 23B shows the ~~simulation~~ measurement results of this invention.

Amend the paragraph starting at page 10, line 5, as follows:

Also, for the sake of description, the first $n^+$-type region 201 shall be the terminal of the protecting element 200 that is connected to the gate terminal G, which is one of the terminals of the FET 100, and the second $n^+$-type region 202 shall be the terminal of the protecting element 200 that is connected to the source terminal S or the drain terminal D, which is the other terminal of the FET 100, in this specification. That is, in Fig. [[1]] 4A, two protecting elements 200 are connected to the FET 100 and the first $n^+$-type region 201 of each is connected via the metal electrode 204 to the gate pad GP and the second $n^+$-type region 202 is connected via the metal

electrode 204 to the drain pad DP or the source pad SP. The metal electrodes 204 form Schottky junctions with the first and second $n^+$-type regions 201 and 202 and parts of the metal electrodes 204 are extended to the semi-insulating substrate 101 to form Schottky junctions with the substrate surface. The structure of the metal electrode 204 is only an example and may be that of either Figs. 2 or Figs. 3.

Amend the paragraph starting at page 28, line 26, as follows:

The β of a b-structure and the electrostatic breakdown voltage shall now be described with reference to Figs. 21. As mentioned above, securing an adequate area of the insulating region 203 is equivalent to securing an adequate region that can become the second current path I2 and thus provides a high protection effect. That is, a predetermined insulating region width β is secured at the side opposite from the opposing surface OS as shown in the plan view of Fig. [[21A]] 21B. Fig. [[21B]] 21A shows the results of the experiment to measure the electrostatic breakdown voltage upon varying the value of β.

Delete the heading at page 35, line 9.